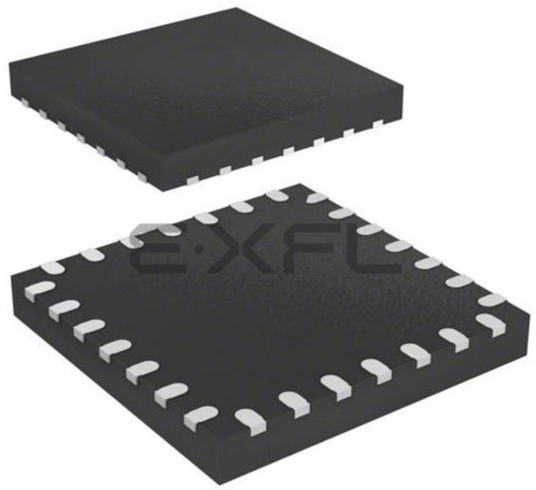

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	24
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN
Supplier Device Package	28-UFQFPN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l011g4u6tr

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Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued)(1)(2)

IPs	Run/Active	Sleep	Low-power run	Low-power sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
Programmable Voltage Detector (PVD)	O	O	O	O	O	O	-	-
Power-on/down reset (POR/PDR)	Y	Y	Y	Y	Y	Y	Y	Y
High Speed Internal (HSI)	O	O	-	-	(3)	-	-	-
High Speed External (HSE)	O	O	O	O	-	-	-	-
Low Speed Internal (LSI)	O	O	O	O	O	-	O	-
Low Speed External (LSE)	O	O	O	O	O	-	O	-
Multi-Speed Internal (MSI)	O	O	Y	Y	-	-	-	-
Inter-Connect Controller	Y	Y	Y	Y	Y	-	-	-
RTC	O	O	O	O	O	O	O	-
RTC Tamper	O	O	O	O	O	O	O	O
Auto WakeUp (AWU)	O	O	O	O	O	-	O	O
USART	O	O	O	O	O(4)	O	-	-
LPUART	O	O	O	O	O(4)	O	-	-
SPI	O	O	O	O	-		-	-
I2C	O	O	O	O	O(5)	O	-	-
ADC	O	O	-	-	-	-	-	-
Temperature sensor	O	O	O	O	O	-	-	-
Comparators	O	O	O	O	O	O	-	-
16-bit timers	O	O	O	O	-	-	-	-
LPTIM	O	O	O	O	O	O	-	-
IWDG	O	O	O	O	O	O	O	O
WWDG	O	O	O	O	-	-	-	-
SysTick Timer	O	O	O	O	-	-	-	-
GPIOs	O	O	O	O	O	O	-	2 pins

3.10 Analog-to-digital converter (ADC)

A native 12-bit, extended to 16-bit through hardware oversampling, analog-to-digital converter is embedded into STM32L011x3/4 devices. It has up to 10 external channels and 2 internal channels (temperature sensor, voltage reference). Three channels, PA0, PA4 and PA5, are fast channels, while the others are standard channels.

The ADC performs conversions in single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

The ADC frequency is independent from the CPU frequency, allowing maximum sampling rate of 1.14 MSPS even with a low CPU speed. The ADC consumption is low at all frequencies (~25 µA at 10 kSPS, ~200 µA at 1MSPS). An auto-shutdown function guarantees that the ADC is powered off except during the active conversion phase.

The ADC can be served by the DMA controller. It can operate from a supply voltage down to 1.65 V.

The ADC features a hardware oversampler up to 256 samples, this improves the resolution to 16 bits (see AN2668).

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all scanned channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) can be internally connected to the ADC start triggers, to allow the application to synchronize A/D conversions and timers.

3.11 Temperature sensor

The temperature sensor (T_{SENSE}) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN18 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode (see *Table 57: Temperature sensor calibration values*).

3.11.1 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value (since no external voltage, V_{REF+}, is available for ADC). The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area (see *Table 20: Embedded internal reference voltage calibration values*). It is accessible in read-only mode.

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V ≤ V_{DD} ≤ 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 11*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 12*.

Figure 11. Pin loading conditions

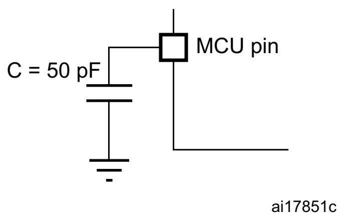
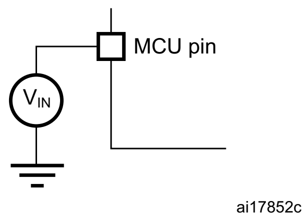
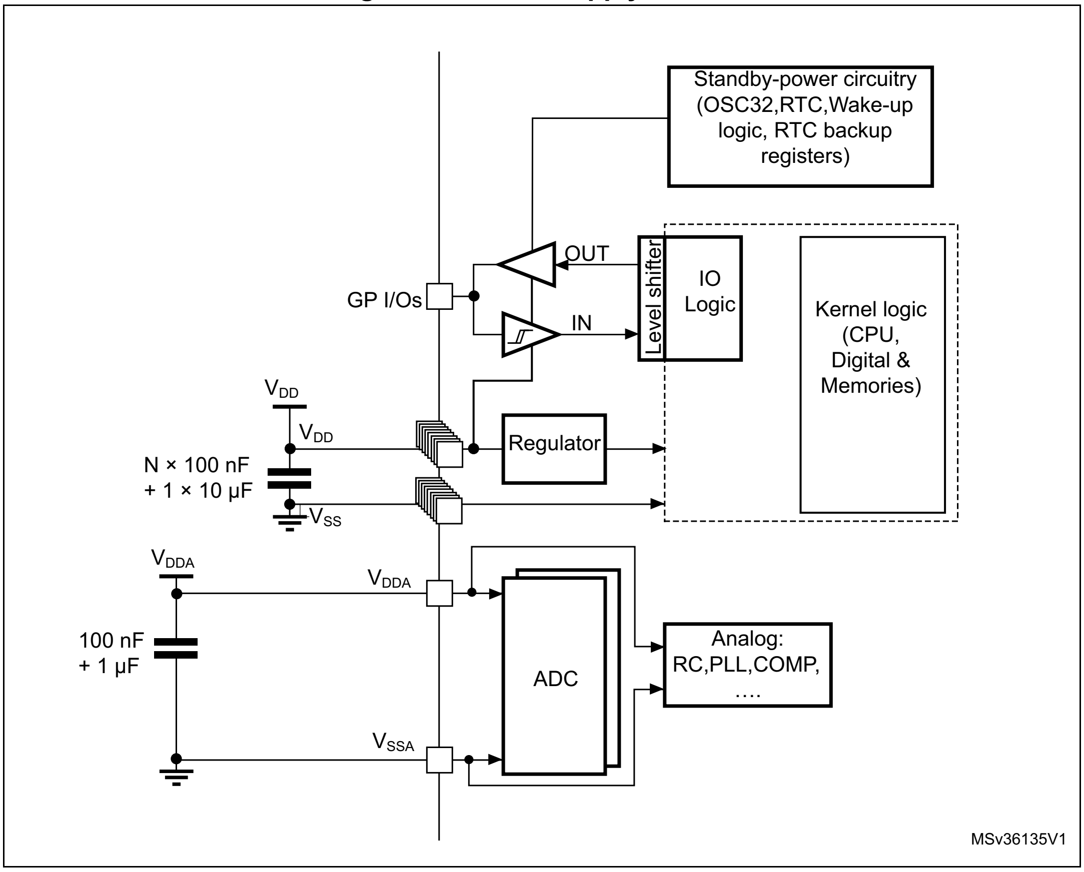


Figure 12. Pin input voltage



6.1.6 Power supply scheme

Figure 13. Power supply scheme



1. On TSSOP14 package, V_{DDA} is internally connected to V_{DD}.
2. V_{SSA} is internally connected to V_{SS} on all packages.

6.1.7 Current consumption measurement

Figure 14. Current consumption measurement scheme

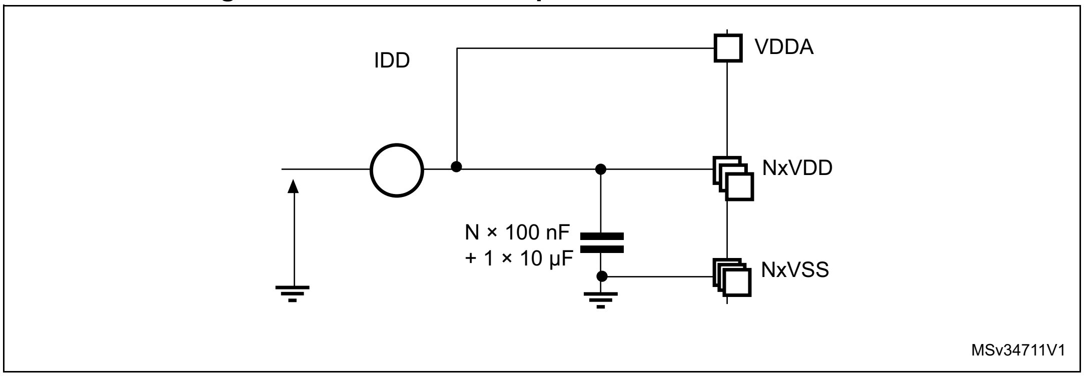


Table 16. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}(2)	Total current into sum of all V_{DD} power lines (source)(1)	105	mA
ΣI_{VSS}(2)	Total current out of sum of all V_{SS} ground lines (sink)(1)	105	
$I_{VDD(PIN)}$	Maximum current into each V_{DD} power pin (source)(1)	100	
$I_{VSS(PIN)}$	Maximum current out of each V_{SS} ground pin (sink)(1)	100	
I_{IO}	Output current sunk by any I/O and control pin except FTf pins	16	
	Output current sunk by FTf pins	22	
	Output current sourced by any I/O and control pin	-16	
$\Sigma I_{IO(PIN)}$(3)	Total output current sunk by sum of all IOs and control pins(4)	45	
	Total output current sourced by sum of all IOs and control pins	-45	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins(2)	90	
	Total output current sourced by sum of all IOs and control pins(2)	-90	
$I_{INJ(PIN)}$	Injected current on FT, FFf, RST and B pins	-5/+0(5)	
	Injected current on TC pin	± 5(6)	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(7)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. These values apply only to STM32L011GxUx part number (UFQFPN28 package).
4. This current consumption must be correctly distributed over all I/Os and control pins. In particular, it must be located the closest possible to the couple of supply and ground, and distributed on both sides.
5. Positive current injection is not possible on these I/Os. A negative injection is induced by V_{IN}<V_{SS}. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 15* for maximum allowed input voltage values.
6. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 15: Voltage characteristics* for the maximum allowed input voltage values.
7. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 17. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

Figure 15. I_{DD} vs V_{DD}, at T_A= 25 °C, Run mode, code running from Flash memory, Range 2, 16 MHz HSE, 1WS

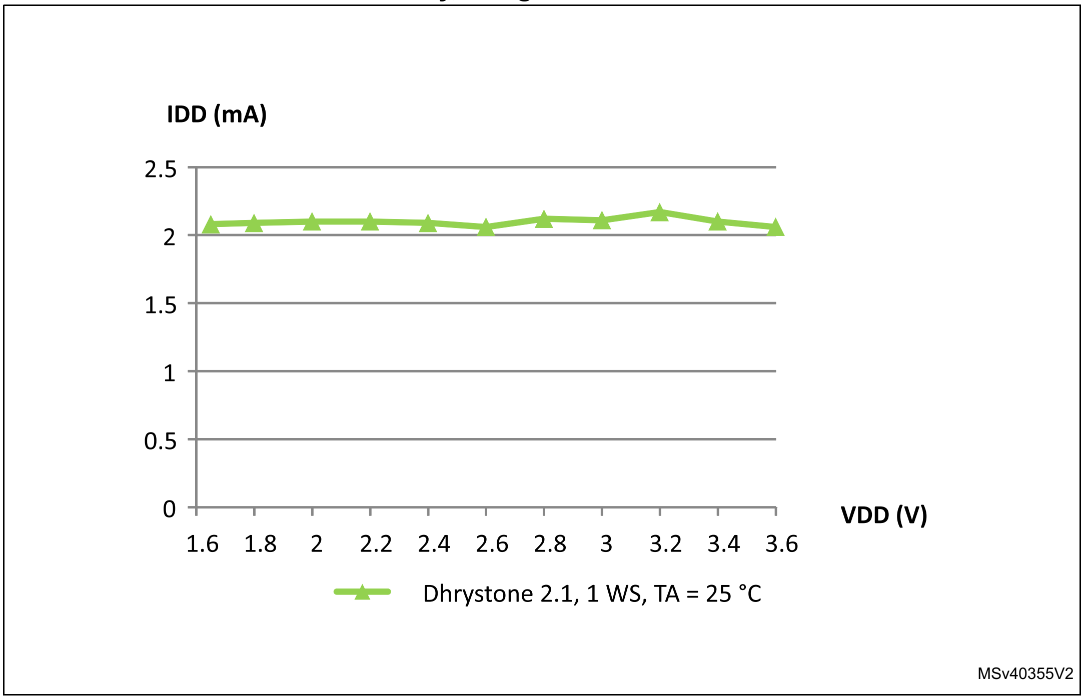


Figure 16. I_{DD} vs V_{DD}, at T_A= 25 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS

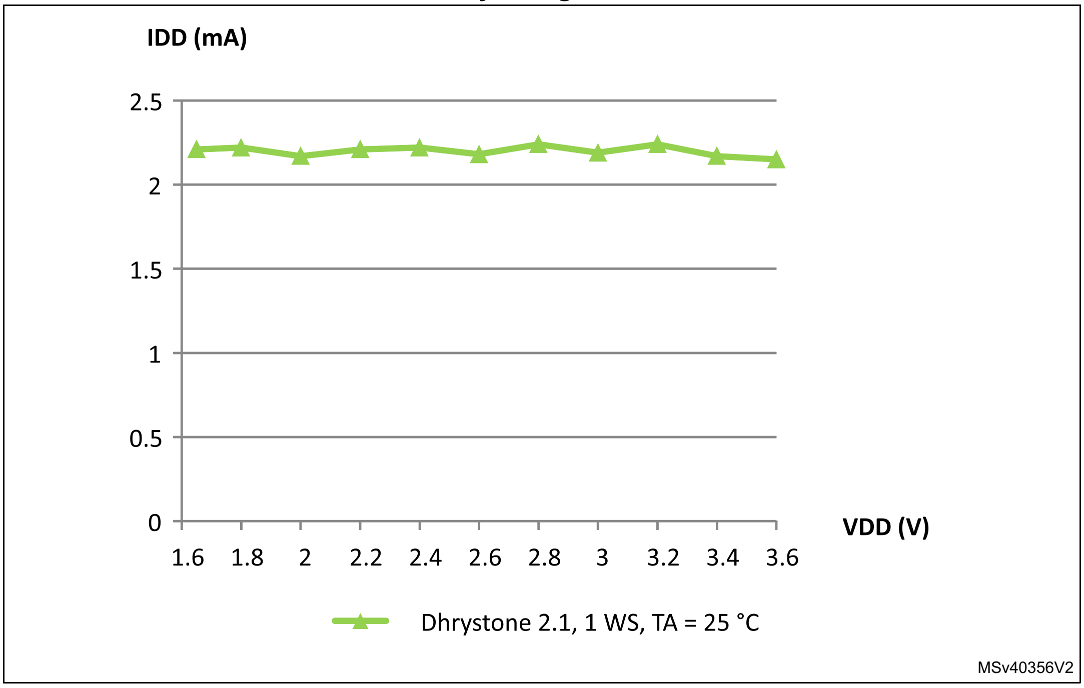


Table 27. Current consumption in Low-power Run mode

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
I_{DD} (LP Run)	Supply current in Low-power run mode	All peripherals OFF, code executed from RAM, Flash switched OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	5.7	8.1	µA
				T_A = 85 °C	6.5	9	
				T_A = 105 °C	8	13	
				T_A = 125 °C	11.5	22	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A =-40 °C to 25 °C	8.7	11	
				T_A = 85 °C	9.5	12	
				T_A = 105 °C	11	15	
				T_A = 125 °C	15	24	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	17	19	
				T_A = 55 °C	17	19.5	
				T_A = 85 °C	17.5	20	
				T_A = 105 °C	19	22	
				T_A = 125 °C	22.5	31	
		All peripherals OFF, code executed from Flash, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	18	22	
				T_A = 85 °C	20	24	
				T_A = 105 °C	22	27	
				T_A = 125 °C	26.5	37	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A = -40 °C to 25 °C	22	25	
				T_A = 85 °C	24	27	
				T_A = 105 °C	26	30	
				T_A = 125 °C	30.5	39	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	32	34	
				T_A = 55 °C	32.5	35	
				T_A = 85 °C	34	37	
				T_A = 105 °C	36	39	
				T_A = 125 °C	40	47	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.

Table 33. Peripheral current consumption in Stop and Standby mode

Symbol	Peripheral	Typical consumption, T_A = 25 °C		Unit
		V_{DD}=1.8 V	V_{DD}=3.0 V	
$I_{DD(PVD / BOR)}$	-	0.6	1	µA
I_{REFINT}	-	1.25	1.3	
-	LSE Low drive	0.11	0.16	
-	LPTIM1, Input 100 Hz	0.01	0.02	
-	LPTIM1, Input 1 MHz	8	9	
-	LPUART1	0.025	0.027	
-	RTC	0.1	0.19	

6.3.5 Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI or HSI16 RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is either the MSI oscillator in the range configured before entering Stop mode, the HSI16 or HSI16/4.
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 18*.

Table 34. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WUSLEEP}$	Wakeup from Sleep mode	f_{HCLK} = 32 MHz	7	8	CPU cycles
$t_{WUSLEEP\_LP}$	Wakeup from Low-power sleep mode, f_{HCLK} = 262 kHz	f_{HCLK} = 262 kHz Flash enabled	7	8	
		f_{HCLK} = 262 kHz Flash switched OFF	9	10	

Table 34. Low-power mode wakeup timings (continued)

Symbol	Parameter	Conditions	Typ	Max	Unit
t_{WUSTOP}	Wakeup from Stop mode, regulator in Run mode	$f_{HCLK} = f_{MSI}$ = 4.2 MHz	5.1	8	µs
		$f_{HCLK} = f_{HSI}$ = 16 MHz	5.1	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	8.1	11	
	Wakeup from Stop mode, regulator in low-power mode	$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 1	5	8	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 2	5	8	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz Voltage range 3	5	8	
		$f_{HCLK} = f_{MSI}$ = 2.1 MHz	7.4	13	
		$f_{HCLK} = f_{MSI}$ = 1.05 MHz	14	23	
		$f_{HCLK} = f_{MSI}$ = 524 kHz	28	38	
		$f_{HCLK} = f_{MSI}$ = 262 kHz	51	65	
		$f_{HCLK} = f_{MSI}$ = 131 kHz	99	120	
		$f_{HCLK} = f_{MSI}$ = 65 kHz	196	260	
		$f_{HCLK} = f_{HSI}$ = 16 MHz	5.1	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	8.2	11	
	Wakeup from Stop mode, regulator in low-power mode, HSI kept running in Stop mode	$f_{HCLK} = f_{HSI}$ = 16 MHz	3.25	-	
	Wakeup from Stop mode, regulator in low-power mode, code running from RAM	$f_{HCLK} = f_{HSI}$ = 16 MHz	4.9	7	
		$f_{HCLK} = f_{HSI}/4$ = 4 MHz	7.9	10	
		$f_{HCLK} = f_{MSI}$ = 4.2 MHz	4.8	8	
$t_{WUSTDBY}$	Wakeup from Standby mode FWU bit = 1	$f_{HCLK} = f_{MSI}$ = 2.1 MHz	65	130	
	Wakeup from Standby mode FWU bit = 0	$f_{HCLK} = f_{MSI}$ = 2.1 MHz	2.2	3	ms

6.3.6 External clock source characteristics

High-speed external user clock generated from an external source

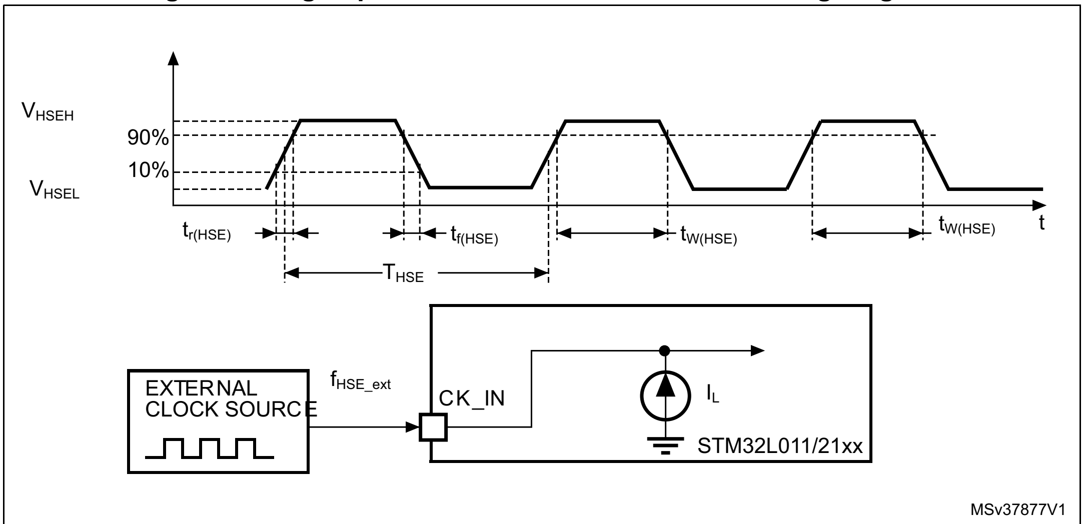
In bypass mode the input pin is a standard GPIO.The external clock signal has to respect the I/O characteristics in *Section 6.3.12*. However, the recommended clock input waveform is shown in *Figure 20*.

Table 35. High-speed external user clock characteristics[1]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	CSS is ON or PLL is used	1	8	32	MHz
		CSS is OFF, PLL not used	0	8	32	MHz
V_{HSEH}	CK_IN input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	CK_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	CK_IN high or low time		12	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	CK_IN rise or fall time		-	-	20	
$C_{in(HSE)}$	CK_IN input capacitance		-	2.6	-	pF
$DuCy_{(HSE)}$	Duty cycle		45	-	55	%
I_L	CK_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production.

Figure 20. High-speed external clock source AC timing diagram



Low-speed external user clock generated from an external source

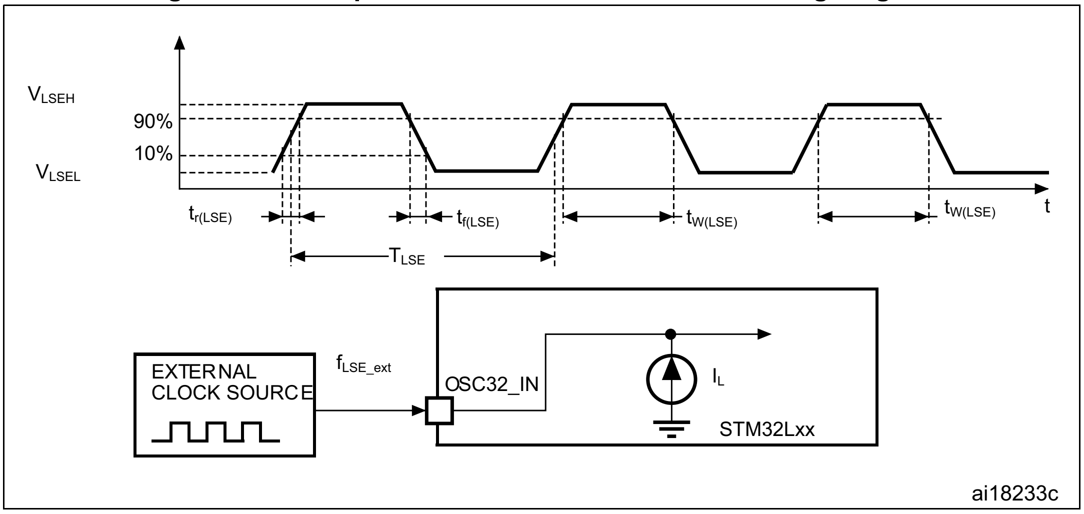
The characteristics given in the following table result from tests performed using a low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in Table 18.

Table 36. Low-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage	-	V_{SS}	-	$0.3V_{DD}$	V
$t_{w(LSE)}$ $t_{w(LSE)}$	OSC32_IN high or low time	-	465	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time	-	-	-	10	ns
$C_{IN(LSE)}$	OSC32_IN input capacitance	-	-	0.6	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production

Figure 21. Low-speed external clock source AC timing diagram



Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in Table 37. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization

6.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the conditions summarized in *Table 18*. All I/Os are CMOS and TTL compliant.

Table 50. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	TC, FT, FTf, RST I/Os	-	-	$0.3V_{DD}$	V
		BOOT0 pin	-	-	$0.14V_{DD}$(1)	
V_{IH}	Input high level voltage	All I/Os except BOOT0 pin	$0.7\ V_{DD}$	-	-	
		BOOT0 pin	$0.15\ V_{DD}+0.56$(1)	-	-	
V_{hys}	I/O Schmitt trigger voltage hysteresis (2)	Standard I/Os	-	$10\%\ V_{DD}$(3)	-	
		BOOT0 pin	-	0.01	-	
I_{lkg}	Input leakage current (4)	$V_{SS} \leq V_{IN} \leq V_{DD}$ All I/Os except BOOT0 and FTf I/Os	-	-	±50	nA
		BOOT0(5) $V_{IN} = V_{DD}$	-	+2	-	µA
		BOOT0 $V_{IN} = V_{SS}$	-	0	-	
		$V_{DD} \leq V_{IN} \leq 5\ V$ FT I/Os	-	-	200	nA
		$V_{DD} \leq V_{IN} \leq 5\ V$ FTf I/Os	-	-	500	
		$V_{DD} \leq V_{IN} \leq 5\ V$ BOOT0	-	-	10	µA
R_{PU}	Weak pull-up equivalent resistor(6)	$V_{IN} = V_{SS}$	30	45	60	kΩ
R_{PD}	Weak pull-down equivalent resistor(6)	$V_{IN} = V_{DD}$	30	45	60	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Guaranteed by characterization, not tested in production
2. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results, not tested in production.
3. With a minimum of 200 mV. Guaranteed by characterization results, not tested in production.
4. The max. value may be exceeded if negative current is injected on adjacent pins.
5. BOOT0/PB9 pin limitation: typical input leakage current = 2 µA and input frequency limited to 10 kHz (1.65 V < V_{DD} < 2.7 V) and 5 MHz (2.7 V < V_{DD} < 3.6 V).
6. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

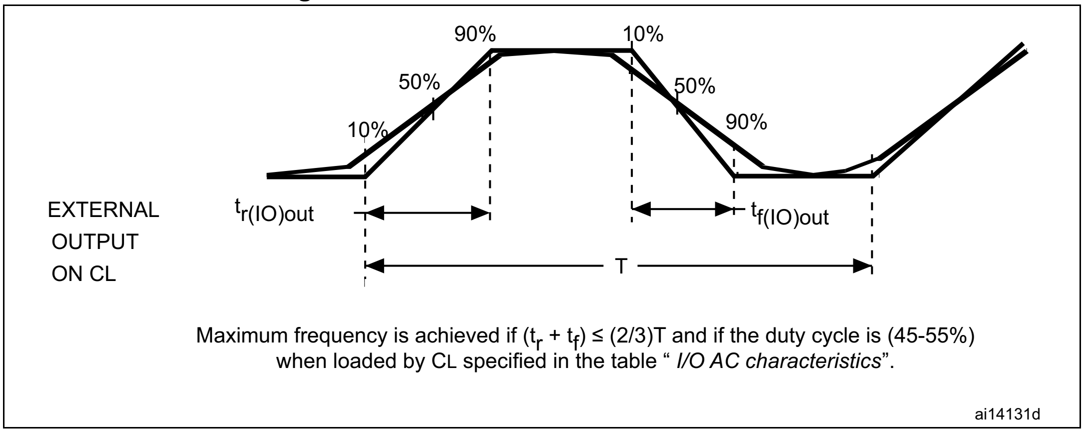
Table 18. All I/Os are CMOS and TTL compliant.

Table 51. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}[1]	Output low level voltage for an I/O pin	CMOS port[2], I_{IO} = +8 mA, 2.7 V ≤ V_{DD} ≤ 3.6 V	-	0.4	V
V_{OH}[3]	Output high level voltage for an I/O pin		V_{DD}-0.4	-	
V_{OL}[1]	Output low level voltage for an I/O pin	TTL port[2], I_{IO} =+ 8 mA, 2.7 V ≤ V_{DD} ≤ 3.6 V	-	0.4	
V_{OH}[3][4]	Output high level voltage for an I/O pin	TTL port[2], I_{IO} = -6 mA, 2.7 V ≤ V_{DD} ≤ 3.6 V	2.4	-	
V_{OL}[1][4]	Output low level voltage for an I/O pin	I_{IO} = +15 mA, 2.7 V ≤ V_{DD} ≤ 3.6 V	-	1.3	
V_{OH}[3][4]	Output high level voltage for an I/O pin	I_{IO} = -15 mA, 2.7 V ≤ V_{DD} ≤ 3.6 V	V_{DD}-1.3	-	
V_{OL}[1][4]	Output low level voltage for an I/O pin	I_{IO} = +4 mA, 1.65 V ≤ V_{DD} < 3.6 V	-	0.45	
V_{OH}[3][4]	Output high level voltage for an I/O pin	I_{IO} = -4 mA, 1.65 V ≤ V_{DD} ≤ 3.6 V	V_{DD}-0.45	-	
V_{OLFM+}[1][4]	Output low level voltage for an FTf I/O pin in Fm+ mode	I_{IO} = 20 mA, 2.7 V ≤ V_{DD} ≤ 3.6 V	-	0.4	
		I_{IO} = 10 mA, 1.65 V ≤ V_{DD} ≤ 3.6 V	-	0.4	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 16*. The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 16*. The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
4. Guaranteed by characterization results, not tested in production.

Figure 26. I/O AC characteristics definition



6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} , except when it is internally driven low (see *Table 53*).

Unless otherwise specified, the parameters given in *Table 53* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 18*.

Table 53. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$[1]	NRST input low level voltage	-	-	-	$0.3V_{DD}$	V
$V_{IH(NRST)}$[1]	NRST input high level voltage	-	$0.39V_{DD}$+ 0.59	-	-	V
$V_{OL(NRST)}$[1]	NRST output low level voltage	I_{OL} = 2 mA 2.7 V < V_{DD} < 3.6 V	-	-	0.4	V
		I_{OL} = 1.5 mA 1.65 V < V_{DD} < 2.7 V	-	-		
$V_{hys(NRST)}$[1]	NRST Schmitt trigger voltage hysteresis	-	-	$10\%V_{DD}$[2]	-	mV
R_{PU}	Weak pull-up equivalent resistor[3]	$V_{IN} = V_{SS}$	30	45	60	kΩ
$V_{F(NRST)}$[1]	NRST input filtered pulse	-	-	-	50	ns
$V_{NF(NRST)}$[1]	NRST input not filtered pulse	-	350	-	-	ns

1. Guaranteed by design, not tested in production.
2. 200 mV minimum value
3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

Table 54. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{CAL} (3)	Calibration time	f_{ADC} = 16 MHz		5.2		µs
		-		83		$1/f_{ADC}$
$W_{LATENCY}$	ADC_DR register write latency	ADC clock = HSI16	1.5 ADC cycles + 2 f_{PCLK} cycles	-	1.5 ADC cycles + 3 f_{PCLK} cycles	-
		ADC clock = PCLK/2	-	4.5	-	f_{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f_{PCLK} cycle
t_{latr} (3)	Trigger conversion latency	$f_{ADC} = f_{PCLK}/2$ = 16 MHz		0.266		µs
		$f_{ADC} = f_{PCLK}/2$		8.5		$1/f_{PCLK}$
		$f_{ADC} = f_{PCLK}/4$ = 8 MHz		0.516		µs
		$f_{ADC} = f_{PCLK}/4$		16.5		$1/f_{PCLK}$
		$f_{ADC} = f_{HSI16}$ = 16 MHz	0.252	-	0.260	µs
$Jitter_{ADC}$	ADC jitter on trigger conversion	$f_{ADC} = f_{HSI16}$	-	1	-	$1/f_{HSI16}$
t_S (3)	Sampling time	f_{ADC} = 16 MHz	0.093	-	10.03	µs
		-	1.5	-	239.5	$1/f_{ADC}$
t_{STAB} (3)	Power-up time	-	0	0	1	µs
t_{ConV} (3)	Total conversion time (including sampling time)	f_{ADC} = 16 MHz	0.875		10.81	µs
		-		14 to 173 (t_S for sampling +12.5 for successive approximation)		$1/f_{ADC}$

1. V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to *Table 55: RAIN max for fADC = 16 MHz*.
2. A current consumption proportional to the APB clock frequency has to be added (see *Table 32: Peripheral current consumption in run or Sleep mode*).
3. Guaranteed by design, not tested in production.
4. Standard channels have an extra protection resistance which depends on supply voltage. Refer to *Table 55: RAIN max for fADC = 16 MHz*.

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The simplified formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 67. SPI characteristics in voltage Range 3 [(1)]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	-	2	MHz
		Slave mode			$2^{(2)}$	
$Duty_{(SCK)}$	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	4Tpclk	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	2Tpclk	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
$t_{su(MI)}$	Data input setup time	Master mode	3	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	16	-	-	
$t_{h(SI)}$		Slave mode	14	-	-	
$t_{a(SO}$	Data output access time	Slave mode	30	-	70	
$t_{dis(SO)}$	Data output disable time	Slave mode	40	-	80	
$t_{v(SO)}$	Data output valid time	Slave mode	-	26.5	47	
		Master mode	-	4	6	
$t_{v(MO)}$	Data output hold time	Slave mode	20	-	-	
$t_{h(SO)}$		Master mode	3	-	-	

1. Guaranteed by characterization results, not tested in production.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)}$ = 0 while $Duty_{(SCK)}$ = 50%.

Figure 30. SPI timing diagram - slave mode and CPHA = 0

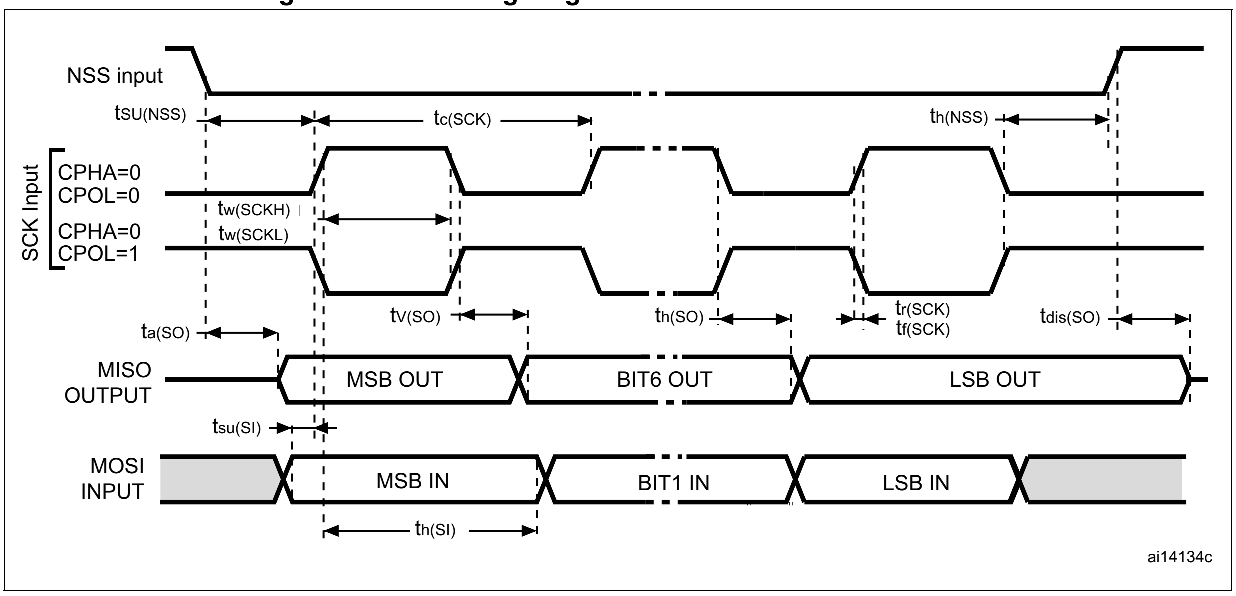
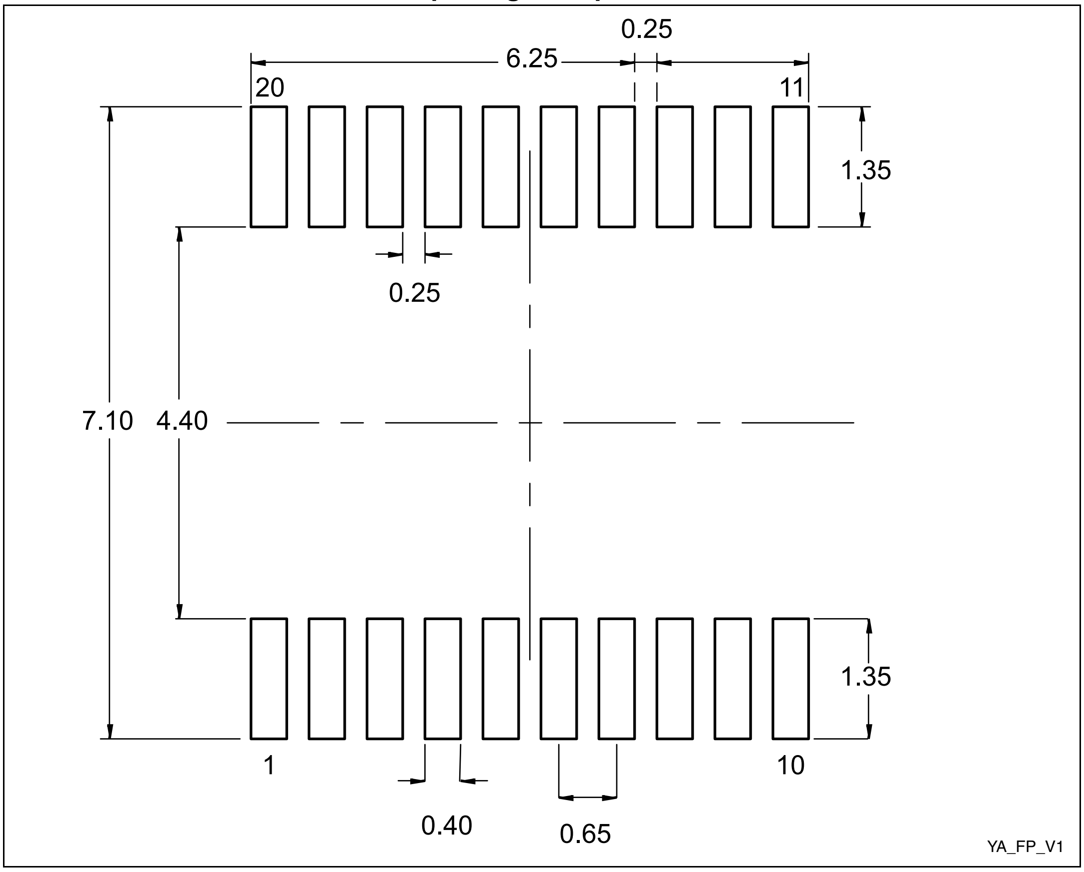


Table 74. TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch, package mechanical data (continued)

Symbol	millimeters			inches[(1)]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
k	0°	-	8°	0°	-	8°
aaa	-	-	0.100	-	-	0.0039

1. Values in inches are converted from mm and rounded to four decimal digits.

Figure 49. TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch, package footprint

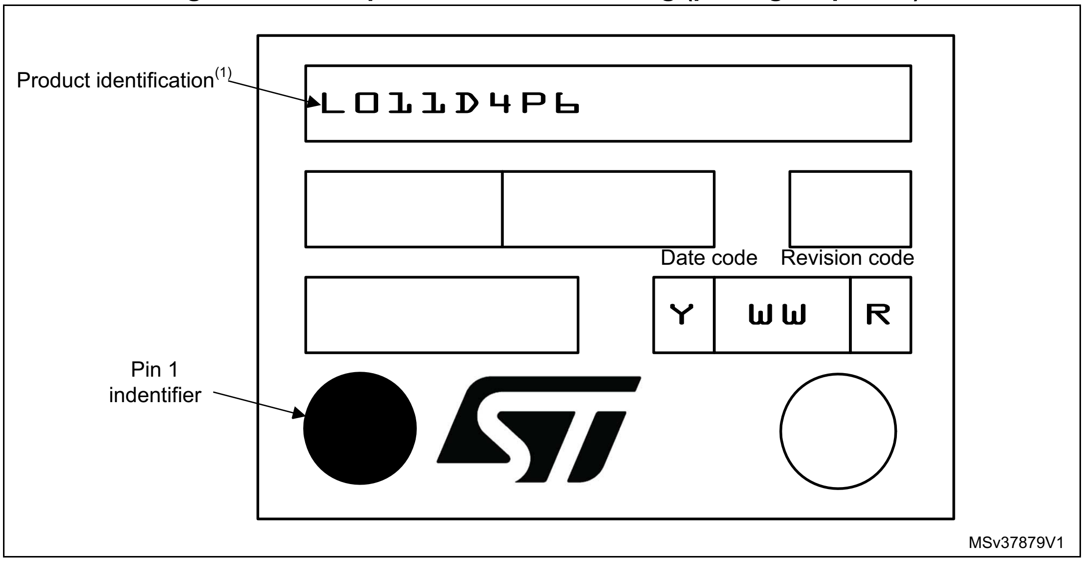


1. Dimensions are expressed in millimeters.

TSSOP14 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

Figure 52. Example of TSSOP14 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.8 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma((V_{DD} - V_{OH}) \times I_{OH})$,

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.